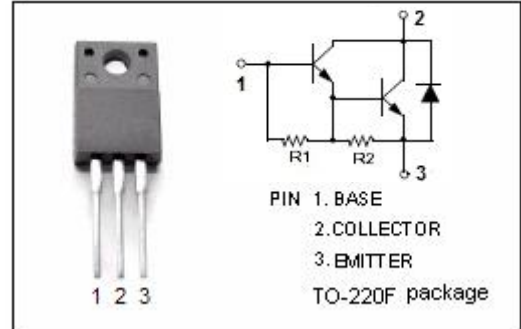


**isc Silicon NPN Darlington Power Transistor**
**2SD2241**
**DESCRIPTION**

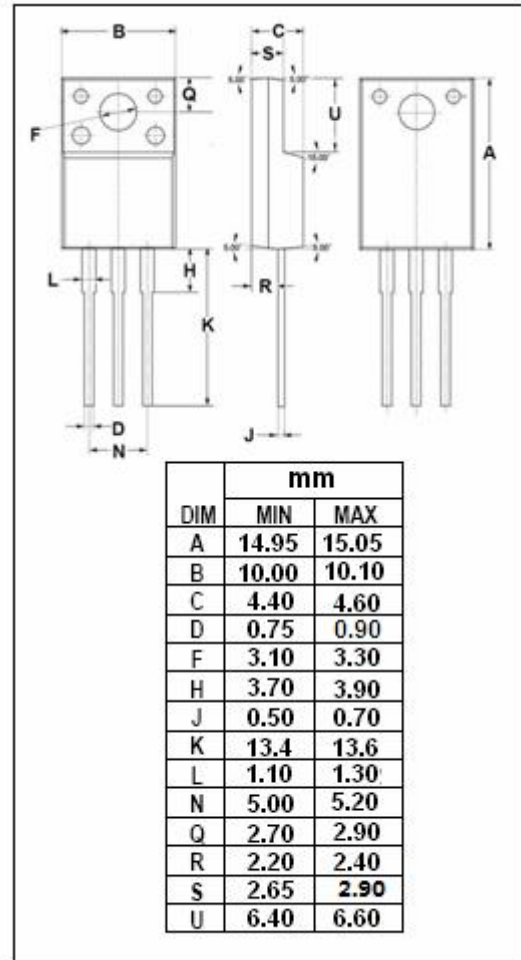
- Collector-Emitter Breakdown Voltage-  
:  $V_{(BR)CEO} = 100V(\text{Min})$
- Collector-Emitter Saturation Voltage-  
:  $V_{CE(sat)} = 1.5V(\text{Max}) @ I_C = 3A$
- High DC Current Gain  
:  $h_{FE} = 2000(\text{Min}) @ I_C = 1.5A, V_{CE} = 3V$
- Complement to Type 2SB1481
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

**APPLICATIONS**

- Designed for switching applications


**ABSOLUTE MAXIMUM RATINGS ( $T_a = 25^\circ\text{C}$ )**

SYMBOL	PARAMETER	VALUE	UNIT
$V_{CBO}$	Collector-Base Voltage	100	V
$V_{CEO}$	Collector-Emitter Voltage	100	V
$V_{EBO}$	Emitter-Base Voltage	5	V
$I_C$	Collector Current-Continuous	4	A
$I_{CM}$	Collector Current-Peak	6	A
$I_B$	Base Current-Continuous	0.3	A
$P_C$	Collector Power Dissipation @ $T_C = 25^\circ\text{C}$	25	W
	Collector Power Dissipation @ $T_a = 25^\circ\text{C}$	2.0	
$T_J$	Junction Temperature	150	$^\circ\text{C}$
$T_{stg}$	Storage Temperature Range	-55~150	$^\circ\text{C}$



**isc Silicon NPN Darlington Power Transistor**
**2SD2241**
**ELECTRICAL CHARACTERISTICS**

 T<sub>c</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 10mA ; I <sub>B</sub> = 0	100			V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 3A; I <sub>B</sub> = 6mA			1.5	V
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 3A; I <sub>B</sub> = 6mA			2.0	V
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = 100V; I <sub>E</sub> = 0			20	μ A
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 5V; I <sub>C</sub> = 0			2.5	mA
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = 1.5A; V <sub>CE</sub> = 2V	2000			
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = 3A; V <sub>CE</sub> = 2V	1000			
V <sub>ECF</sub>	C-E Diode Forward Voltage	I <sub>E</sub> = 1A; I <sub>B</sub> = 0			2.0	V

## Switching times

t <sub>on</sub>	Turn-on Time	I <sub>B1</sub> = I <sub>B2</sub> = 6mA; R <sub>L</sub> = 10 Ω ; V <sub>CC</sub> ≈ 30V P <sub>W</sub> =20 μ s; Duty Cycle ≤ 1%		0.2		μ s
t <sub>stg</sub>	Storage Time			1.5		μ s
t <sub>f</sub>	Fall Time			0.6		μ s

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